

FIS920030085

IN THE SPECIFICATION

Please delete the period in the second sentence of paragraph [0004] with the following amended sentence as follows:

[0004] A technique used to deposit insulators that is being used more frequently in densely-packed semiconductor devices having small feature sizes and high aspect ratios is high density plasma chemical vapor deposition (HDP-CVD). HDP-CVD has been used in the BEOL in the past, and is also being used in the front-end-of-line (FEOL) for shallow trench isolation (STI). Generally, in HDP-CVD ions and electrons are generated in an inductively coupled radiofrequency (RF) plasma[.] (no electrode in non-capacitively coupled plasmas). An RF biasing power is applied to another (substrate -holding) electrode to create a significant ion bombardment (i.e., sputter etching) component during deposition. For gap filling, HDP-CVD processes provide simultaneous deposition and etching in which loosely deposited films or "deposited species" over planar or topographical surfaces are sputtered off by reactive ions and radicals during deposition. In this manner, voids can be eliminated during the gap fill process. However, HDP-CVD is proving a challenge with today's rapidly increasing high aspect ratio features, which are approaching 4:1 and higher.

Please insert a space in the first sentence of paragraph [0015] after "Figure 1", amended sentence as follows:

[0015] Figure 1 illustrates a cross-sectional view of a prior art DRAM having voids in the HDP-CVD insulating material between isolation regions or trenches;